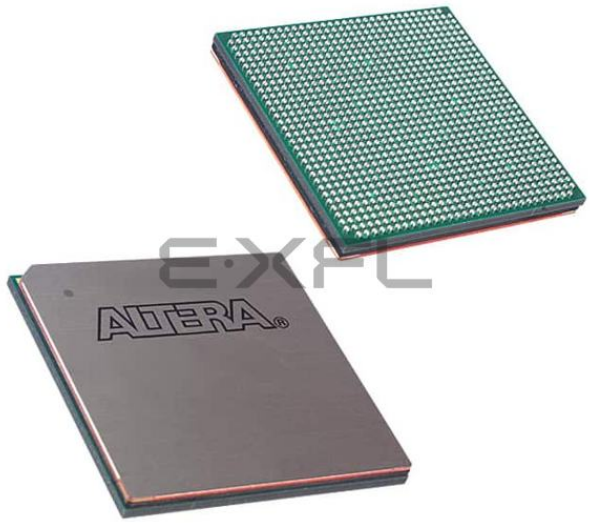


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

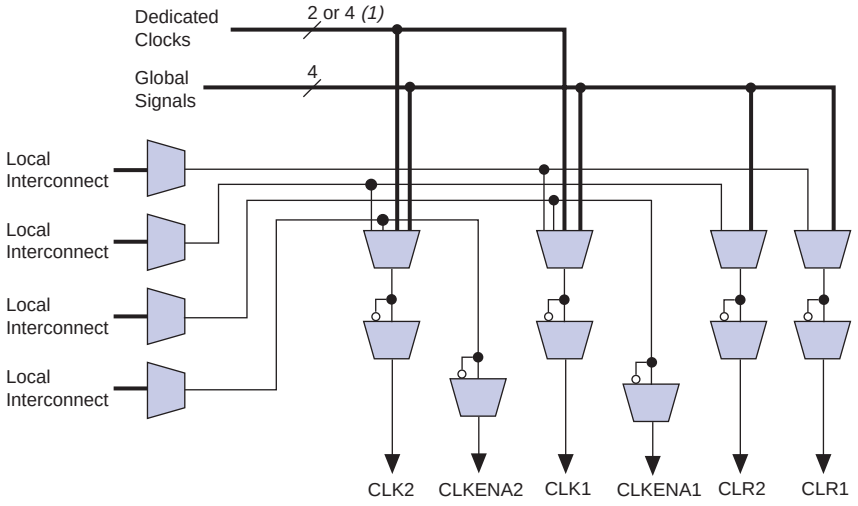
Details	
Product Status	Obsolete
Number of LABs/CLBs	5184
Number of Logic Elements/Cells	51840
Total RAM Bits	442368
Number of I/O	808
Number of Gates	2392000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	1020-BBGA
Supplier Device Package	1020-FBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k1500efc33-1

Table 8. Comparison of APEX 20K & APEX 20KE Features

Feature	APEX 20K Devices	APEX 20KE Devices
MultiCore system integration	Full support	Full support
SignalTap logic analysis	Full support	Full support
32/64-Bit, 33-MHz PCI	Full compliance in -1, -2 speed grades	Full compliance in -1, -2 speed grades
32/64-Bit, 66-MHz PCI	-	Full compliance in -1 speed grade
MultiVolt I/O	2.5-V or 3.3-V V_{CCIO} V_{CCIO} selected for device Certain devices are 5.0-V tolerant	1.8-V, 2.5-V, or 3.3-V V_{CCIO} V_{CCIO} selected block-by-block 5.0-V tolerant with use of external resistor
ClockLock support	Clock delay reduction 2× and 4× clock multiplication	Clock delay reduction $m/(n \times v)$ or $m/(n \times k)$ clock multiplication Drive ClockLock output off-chip External clock feedback ClockShift LVDS support Up to four PLLs ClockShift, clock phase adjustment
Dedicated clock and input pins	Six	Eight
I/O standard support	2.5-V, 3.3-V, 5.0-V I/O 3.3-V PCI Low-voltage complementary metal-oxide semiconductor (LVCMOS) Low-voltage transistor-to-transistor logic (LVTTL)	1.8-V, 2.5-V, 3.3-V, 5.0-V I/O 2.5-V I/O 3.3-V PCI and PCI-X 3.3-V Advanced Graphics Port (AGP) Center tap terminated (CTT) GTL+ LVCMOS LVTTL True-LVDS and LVPECL data pins (in EP20K300E and larger devices) LVDS and LVPECL signaling (in all BGA and FineLine BGA devices) LVDS and LVPECL data pins up to 156 Mbps (in -1 speed grade devices) HSTL Class I PCI-X SSTL-2 Class I and II SSTL-3 Class I and II
Memory support	Dual-port RAM FIFO RAM ROM	CAM Dual-port RAM FIFO RAM ROM

The programmable register also supports an asynchronous clear function. Within the ESB, two asynchronous clears are generated from global signals and the local interconnect. Each macrocell can either choose between the two asynchronous clear signals or choose to not be cleared. Either of the two clear signals can be inverted within the ESB. Figure 15 shows the ESB control logic when implementing product-terms.

Figure 15. ESB Product-Term Mode Control Logic



Note to Figure 15:
(1) APEX 20KE devices have four dedicated clocks.

Parallel Expanders

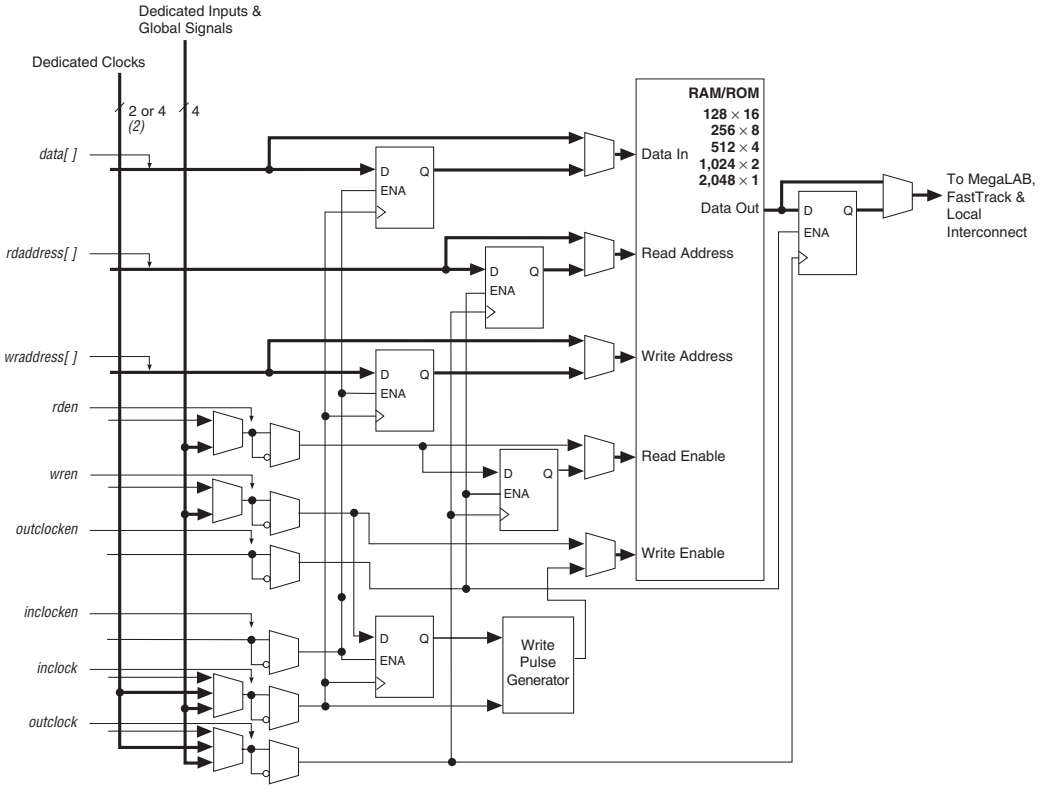
Parallel expanders are unused product terms that can be allocated to a neighboring macrocell to implement fast, complex logic functions. Parallel expanders allow up to 32 product terms to feed the macrocell OR logic directly, with two product terms provided by the macrocell and 30 parallel expanders provided by the neighboring macrocells in the ESB.

The Quartus II software Compiler can allocate up to 15 sets of up to two parallel expanders per set to the macrocells automatically. Each set of two parallel expanders incurs a small, incremental timing delay. Figure 16 shows the APEX 20K parallel expanders.

Read/Write Clock Mode

The read/write clock mode contains two clocks. One clock controls all registers associated with writing: data input, WE, and write address. The other clock controls all registers associated with reading: read enable (RE), read address, and data output. The ESB also supports clock enable and asynchronous clear signals; these signals also control the read and write registers independently. Read/write clock mode is commonly used for applications where reads and writes occur at different system frequencies. Figure 20 shows the ESB in read/write clock mode.

Figure 20. ESB in Read/Write Clock Mode *Note (1)*



Notes to Figure 20:

(1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.
(2) APEX 20KE devices have four dedicated clocks.

Implementing Logic in ROM

In addition to implementing logic with product terms, the ESB can implement logic functions when it is programmed with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of ESBs. The large capacity of ESBs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or distributed RAM blocks. Parameterized functions such as LPM functions can take advantage of the ESB automatically. Further, the Quartus II software can implement portions of a design with ESBs where appropriate.

Programmable Speed/Power Control

APEX 20K ESBs offer a high-speed mode that supports very fast operation on an ESB-by-ESB basis. When high speed is not required, this feature can be turned off to reduce the ESB's power dissipation by up to 50%. ESBs that run at low power incur a nominal timing delay adder. This Turbo Bit™ option is available for ESBs that implement product-term logic or memory functions. An ESB that is not used will be powered down so that it does not consume DC current.

Designers can program each ESB in the APEX 20K device for either high-speed or low-power operation. As a result, speed-critical paths in the design can run at high speed, while the remaining paths operate at reduced power.

I/O Structure

The APEX 20K IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data requiring fast setup times, or as an output register for data requiring fast clock-to-output performance. IOEs can be used as input, output, or bidirectional pins. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The Quartus II software Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Because the APEX 20K IOE offers one output enable per pin, the Quartus II software Compiler can emulate open-drain operation efficiently.

The APEX 20K IOE includes programmable delays that can be activated to ensure zero hold times, minimum clock-to-output times, input IOE register-to-core register transfers, or core-to-output IOE register transfers. A path in which a pin directly drives a register may require the delay to ensure zero hold time, whereas a path in which a pin drives a register through combinatorial logic may not require the delay.

Table 10 describes the APEX 20K programmable delays and their logic options in the Quartus II software.

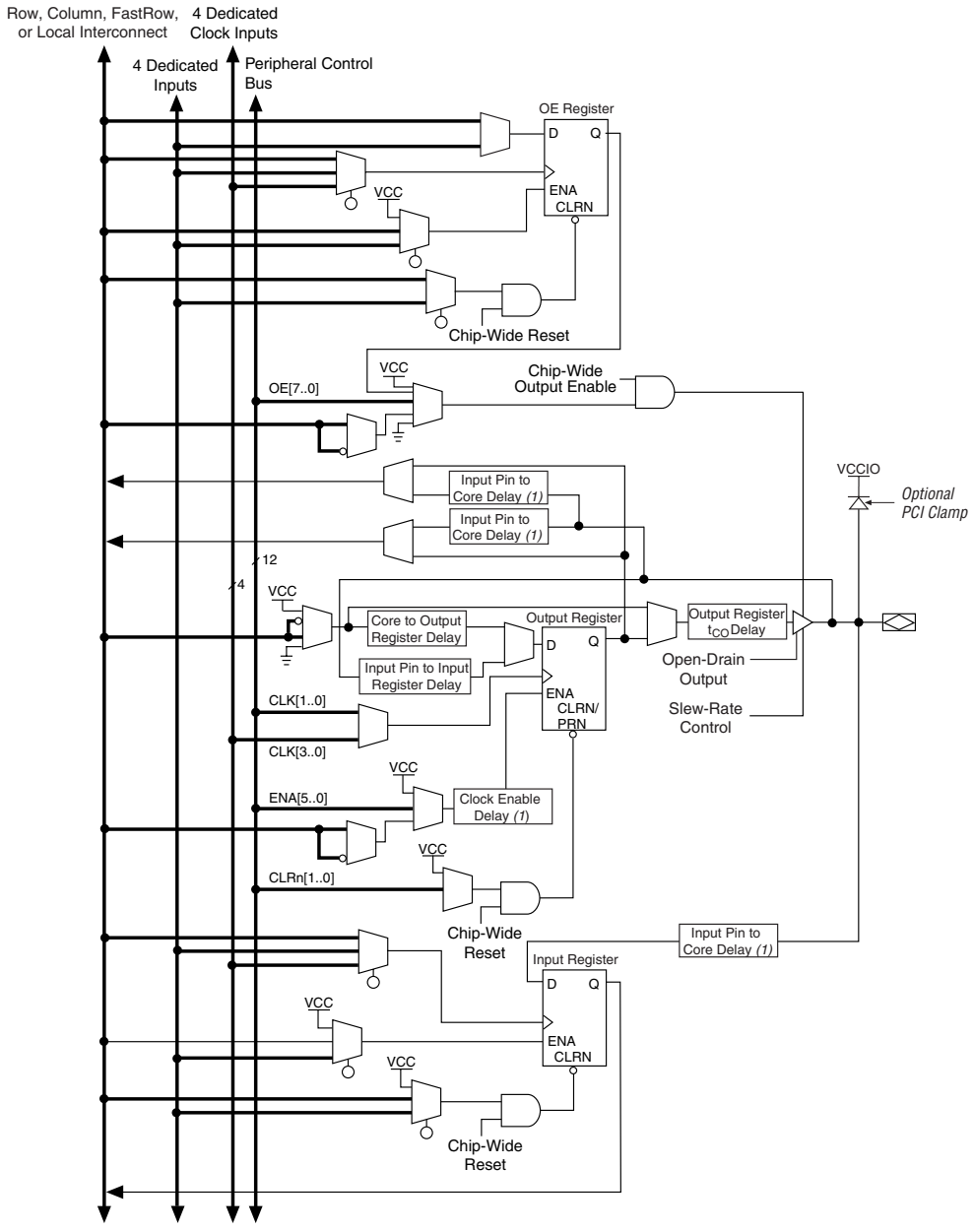
Table 10. APEX 20K Programmable Delay Chains

Programmable Delays	Quartus II Logic Option
Input pin to core delay	Decrease input delay to internal cells
Input pin to input register delay	Decrease input delay to input register
Core to output register delay	Decrease input delay to output register
Output register t_{CO} delay	Increase delay to output pin

The Quartus II software compiler can program these delays automatically to minimize setup time while providing a zero hold time. Figure 25 shows how fast bidirectional I/Os are implemented in APEX 20K devices.

The register in the APEX 20K IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, the register cannot be asynchronously cleared or preset. This feature is useful for cases where the APEX 20K device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Figure 26. APEX 20KE Bidirectional I/O Registers *Notes (1), (2)*



Notes to Figure 26:

(1) This programmable delay has four settings: off and three levels of delay.

(2) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

For designs that require both a multiplied and non-multiplied clock, the clock trace on the board can be connected to CLK2p. Table 14 shows the combinations supported by the ClockLock and ClockBoost circuitry. The CLK2p pin can feed both the ClockLock and ClockBoost circuitry in the APEX 20K device. However, when both circuits are used, the other clock pin (CLK1p) cannot be used.

Table 14. Multiplication Factor Combinations

Clock 1	Clock 2
×1	×1
×1, ×2	×2
×1, ×2, ×4	×4

APEX 20KE ClockLock Feature

APEX 20KE devices include an enhanced ClockLock feature set. These devices include up to four PLLs, which can be used independently. Two PLLs are designed for either general-purpose use or LVDS use (on devices that support LVDS I/O pins). The remaining two PLLs are designed for general-purpose use. The EP20K200E and smaller devices have two PLLs; the EP20K300E and larger devices have four PLLs.

The following sections describe some of the features offered by the APEX 20KE PLLs.

External PLL Feedback

The ClockLock circuit's output can be driven off-chip to clock other devices in the system; further, the feedback loop of the PLL can be routed off-chip. This feature allows the designer to exercise fine control over the I/O interface between the APEX 20KE device and another high-speed device, such as SDRAM.

Clock Multiplication

The APEX 20KE ClockBoost circuit can multiply or divide clocks by a programmable number. The clock can be multiplied by $m/(n \times k)$ or $m/(n \times v)$, where m and k range from 2 to 160, and n and v range from 1 to 16. Clock multiplication and division can be used for time-domain multiplexing and other functions, which can reduce design LE requirements.

Table 21. 32-Bit APEX 20K Device IDCODE

Device	IDCODE (32 Bits) *(1)*			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer Identity (11 Bits)	1 (1 Bit) *(2)*
EP20K30E	0000	1000 0000 0011 0000	000 0110 1110	1
EP20K60E	0000	1000 0000 0110 0000	000 0110 1110	1
EP20K100	0000	0000 0100 0001 0110	000 0110 1110	1
EP20K100E	0000	1000 0001 0000 0000	000 0110 1110	1
EP20K160E	0000	1000 0001 0110 0000	000 0110 1110	1
EP20K200	0000	0000 1000 0011 0010	000 0110 1110	1
EP20K200E	0000	1000 0010 0000 0000	000 0110 1110	1
EP20K300E	0000	1000 0011 0000 0000	000 0110 1110	1
EP20K400	0000	0001 0110 0110 0100	000 0110 1110	1
EP20K400E	0000	1000 0100 0000 0000	000 0110 1110	1
EP20K600E	0000	1000 0110 0000 0000	000 0110 1110	1
EP20K1000E	0000	1001 0000 0000 0000	000 0110 1110	1

Notes to Table 21:
(1) The most significant bit (MSB) is on the left.
(2) The IDCODE's least significant bit (LSB) is always 1.

Figure 31 shows the timing requirements for the JTAG signals.

Figure 31. APEX 20K JTAG Waveforms

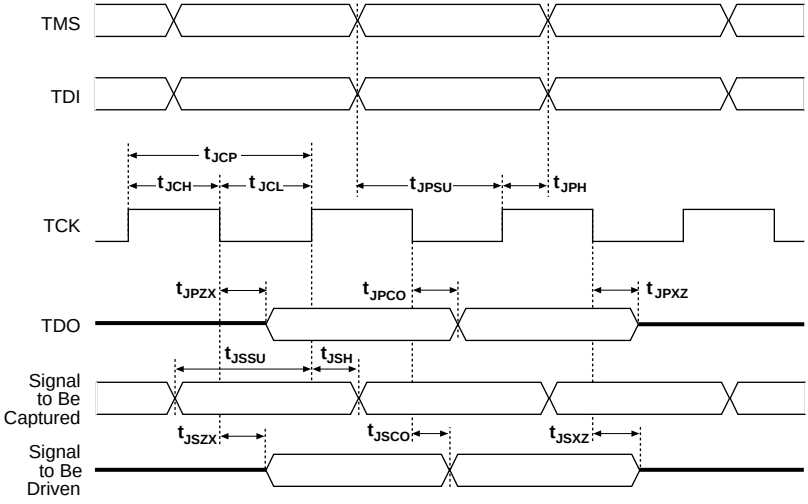


Table 24. APEX 20K 5.0-V Tolerant Device Recommended Operating Conditions *Note (2)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(4), (5)*	2.375 (2.375)	2.625 (2.625)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(4), (5)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(4), (5)*	2.375 (2.375)	2.625 (2.625)	V
V_I	Input voltage	*(3), (6)*	–0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 1 of 2) *Notes (2), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7, 0.5 × V_{CCIO} *(9)*		5.75	V
V_{IL}	Low-level input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(9)*	V
V_{OH}	3.3-V high-level TTL output voltage	I_{OH} = –8 mA DC, V_{CCIO} = 3.00 V *(10)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(10)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(10)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(10)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(10)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(10)*	1.7			V

Table 26. APEX 20K 5.0-V Tolerant Device Capacitance *Notes (2), (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 23 through 26:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) All APEX 20K devices are 5.0-V tolerant.
(3) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(4) Numbers in parentheses are for industrial-temperature-range devices.
(5) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(6) All pins, including dedicated inputs, clock I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A = 25° C, V_{CCINT} = 2.5 V, and V_{CCIO} = 2.5 or 3.3 V.
(8) These values are specified in the APEX 20K device recommended operating conditions, shown in Table 26 on page 62.
(9) The APEX 20K input buffers are compatible with 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant when V_{CCIO} and V_{CCINT} meet the relationship shown in Figure 33 on page 68.
(10) The I_{OH} parameter refers to high-level TTL, PCI or CMOS output current.
(11) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(12) This value is specified for normal device operation. The value may vary during power-up.
(13) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(14) Capacitance is sample-tested only.

Tables 27 through 30 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 1.8-V APEX 20KE devices.

Table 27. APEX 20KE Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	2.5	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–0.5	4.6	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Table 29. APEX 20KE Device DC Operating Conditions *Notes (7), (8), (9)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level LVTTL, CMOS, or 3.3-V PCI input voltage		1.7, 0.5 × V_{CCIO} *(10)*		4.1	V
V_{IL}	Low-level LVTTL, CMOS, or 3.3-V PCI input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(10)*	V
V_{OH}	3.3-V high-level LVTTL output voltage	I_{OH} = –12 mA DC, V_{CCIO} = 3.00 V *(11)*	2.4			V
	3.3-V high-level LVCMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(11)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(11)*	1.7			V
V_{OL}	3.3-V low-level LVTTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(12)*			0.4	V
	3.3-V low-level LVCMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(12)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(12)*			0.1 × V_{CCIO}	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(12)*			0.7	V
I_I	Input pin leakage current	V_I = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(14)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(14)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(14)*	60		150	kΩ

All specifications are always representative of worst-case supply voltage and junction temperature conditions. All output-pin-timing specifications are reported for maximum driver strength.

Figure 36 shows the f_{MAX} timing model for APEX 20K devices.

Figure 36. APEX 20K f_{MAX} Timing Model

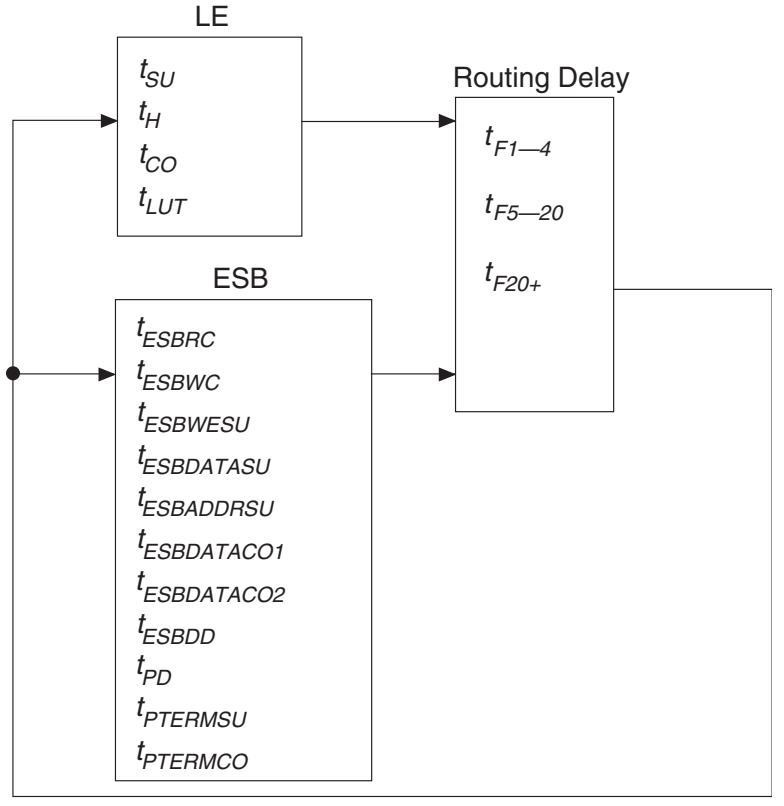


Figure 37 shows the f_{MAX} timing model for APEX 20KE devices. These parameters can be used to estimate f_{MAX} for multiple levels of logic. Quartus II software timing analysis should be used for more accurate timing information.

Note to Tables 32 and 33:
(1) These timing parameters are sample-tested only.

Tables 34 through 37 show APEX 20KE LE, ESB, routing, and functional timing microparameters for the f_{MAX} timing model.

Table 34. APEX 20KE LE Timing Microparameters

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in to data-out

Table 35. APEX 20KE ESB Timing Microparameters

Symbol	Parameter
t_{ESBARC}	ESB Asynchronous read cycle time
t_{ESBSRC}	ESB Synchronous read cycle time
t_{ESBAWC}	ESB Asynchronous write cycle time
t_{ESBSWC}	ESB Synchronous write cycle time
$t_{ESBWASU}$	ESB write address setup time with respect to WE
t_{ESBWAH}	ESB write address hold time with respect to WE
$t_{ESBWDSU}$	ESB data setup time with respect to WE
t_{ESBWDH}	ESB data hold time with respect to WE
$t_{ESBRASU}$	ESB read address setup time with respect to RE
t_{ESBRAH}	ESB read address hold time with respect to RE
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
t_{ESBWEH}	ESB WE hold time after clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBDATAH}$	ESB data hold time after clock when using input register
$t_{ESBWADDRSU}$	ESB write address setup time before clock when using input registers
$t_{ESBRADDRSU}$	ESB read address setup time before clock when using input registers
$t_{ESBDATACO1}$	ESB clock-to-output delay when using output registers
$t_{ESBDATACO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB Macrocell input to non-registered output
$t_{PTERMSU}$	ESB Macrocell register setup time before clock
$t_{PTERMCO}$	ESB Macrocell register clock-to-output delay

Table 46. EP20K200 External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (1)	1.9		2.3		2.6		ns
$t_{INHBIDIR}$ (1)	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$ (1)	2.0	4.6	2.0	5.6	2.0	6.8	ns
$t_{XZBIDIR}$ (1)		5.0		5.9		6.9	ns
$t_{ZXBIDIR}$ (1)		5.0		5.9		6.9	ns
$t_{INSUBIDIR}$ (2)	1.1		1.2		–		ns
$t_{INHBIDIR}$ (2)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (2)	0.5	2.7	0.5	3.1	–	–	ns
$t_{XZBIDIR}$ (2)		4.3		5.0		–	ns
$t_{ZXBIDIR}$ (2)		4.3		5.0		–	ns

Table 47. EP20K400 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU} (1)	1.4		1.8		2.0		ns
t_{INH} (1)	0.0		0.0		0.0		ns
t_{OUTCO} (1)	2.0	4.9	2.0	6.1	2.0	7.0	ns
t_{INSU} (2)	0.4		1.0		–		ns
t_{INH} (2)	0.0		0.0		–		ns
t_{OUTCO} (2)	0.5	3.1	0.5	4.1	–	–	ns

Table 48. EP20K400 External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (1)	1.4		1.8		2.0		ns
$t_{INHBIDIR}$ (1)	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$ (1)	2.0	4.9	2.0	6.1	2.0	7.0	ns
$t_{XZBIDIR}$ (1)		7.3		8.9		10.3	ns
$t_{ZXBIDIR}$ (1)		7.3		8.9		10.3	ns
$t_{INSUBIDIR}$ (2)	0.5		1.0		–		ns
$t_{INHBIDIR}$ (2)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (2)	0.5	3.1	0.5	4.1	–	–	ns
$t_{XZBIDIR}$ (2)		6.2		7.6		–	ns
$t_{ZXBIDIR}$ (2)		6.2		7.6		–	ns

Tables 55 through 60 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K60E APEX 20KE devices.

Table 55. EP20K60E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.17		0.15		0.16		ns
t_{H}	0.32		0.33		0.39		ns
t_{CO}		0.29		0.40		0.60	ns
t_{LUT}		0.77		1.07		1.59	ns

Table 56. EP20K60E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.83		2.57		3.79	ns
t_{ESBSRC}		2.46		3.26		4.61	ns
t_{ESBAWC}		3.50		4.90		7.23	ns
t_{ESBSWC}		3.77		4.90		6.79	ns
$t_{ESBWASU}$	1.59		2.23		3.29		ns
t_{ESBWAH}	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.75		2.46		3.62		ns
t_{ESBWDH}	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.76		2.47		3.64		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.68		2.49		3.87		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.08		0.43		1.04		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.29		0.72		1.46		ns
$t_{ESBRADDRSU}$	0.36		0.81		1.58		ns
$t_{ESBDATACO1}$		1.06		1.24		1.55	ns
$t_{ESBDATACO2}$		2.39		3.35		4.94	ns
t_{ESBDD}		3.50		4.90		7.23	ns
t_{PD}		1.72		2.41		3.56	ns
$t_{PTERMSU}$	0.99		1.56		2.55		ns
$t_{PTERMCO}$		1.07		1.26		1.08	ns

Table 86. EP20K400E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.67		1.91		1.99	ns
t_{ESBSRC}		2.30		2.66		2.93	ns
t_{ESBAWC}		3.09		3.58		3.99	ns
t_{ESBSWC}		3.01		3.65		4.05	ns
$t_{ESBWASU}$	0.54		0.63		0.65		ns
t_{ESBWAH}	0.36		0.43		0.42		ns
$t_{ESBWDSU}$	0.69		0.77		0.84		ns
t_{ESBWDH}	0.36		0.43		0.42		ns
$t_{ESBRASU}$	1.61		1.77		1.86		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.35		1.47		1.61		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.18		-0.30		-0.27		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	-0.02		-0.11		-0.03		ns
$t_{ESBRADDRSU}$	0.06		-0.01		-0.05		ns
$t_{ESBDATACO1}$		1.16		1.40		1.54	ns
$t_{ESBDATACO2}$		2.18		2.55		2.85	ns
t_{ESBDD}		2.73		3.17		3.58	ns
t_{PD}		1.57		1.83		2.07	ns
$t_{PTERMSU}$	0.92		0.99		1.18		ns
$t_{PTERMCO}$		1.18		1.43		1.17	ns

Table 102. EP20K1000E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	3.22		3.33		3.51		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.75	2.00	6.33	2.00	6.90	ns
$t_{XZBIDIR}$		6.31		7.09		7.76	ns
$t_{ZXBIDIR}$		6.31		7.09		7.76	ns
$t_{INSUBIDIRPLL}$	3.25		3.26				ns
$t_{INHBIDIRPLL}$	0.00		0.00				ns
$t_{OUTCOBIDIRPLL}$	0.50	2.25	0.50	2.99			ns
$t_{XZBIDIRPLL}$		2.81		3.80			ns
$t_{ZXBIDIRPLL}$		2.81		3.80			ns

Tables 103 through 108 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K1500E APEX 20KE devices.

Table 103. EP20K1500E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.25		0.25		0.25		ns
t_{H}	0.25		0.25		0.25		ns
t_{CO}		0.28		0.32		0.33	ns
t_{LUT}		0.80		0.95		1.13	ns

Table 104. EP20K1500E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.78		2.02		1.95	ns
t_{ESBSRC}		2.52		2.91		3.14	ns
t_{ESBAWC}		3.52		4.11		4.40	ns
t_{ESBSWC}		3.23		3.84		4.16	ns
$t_{ESBWASU}$	0.62		0.67		0.61		ns
t_{ESBWAH}	0.41		0.55		0.55		ns
$t_{ESBWDSU}$	0.77		0.79		0.81		ns
t_{ESBWDH}	0.41		0.55		0.55		ns
$t_{ESBRASU}$	1.74		1.92		1.85		ns
t_{ESBRAH}	0.00		0.01		0.23		ns
$t_{ESBWESU}$	2.07		2.28		2.41		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.25		0.27		0.29		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.11		0.04		0.11		ns
$t_{ESBRADDRSU}$	0.14		0.11		0.16		ns
$t_{ESBDATACO1}$		1.29		1.50		1.63	ns
$t_{ESBDATACO2}$		2.55		2.99		3.22	ns
t_{ESBDD}		3.12		3.57		3.85	ns
t_{PD}		1.84		2.13		2.32	ns
$t_{PTERMSU}$	1.08		1.19		1.32		ns
$t_{PTERMCO}$		1.31		1.53		1.66	ns

Table 105. EP20K1500E f_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.28		0.28		0.28	ns
t_{F5-20}		1.36		1.50		1.62	ns
t_{F20+}		4.43		4.48		5.07	ns

Version 4.1

APEX 20K Programmable Logic Device Family Data Sheet version 4.1 contains the following changes:

- t_{ESBWEH} added to Figure 37 and Tables 35, 50, 56, 62, 68, 74, 86, 92, 97, and 104.
- Updated EP20K300E device internal and external timing numbers in Tables 79 through 84.